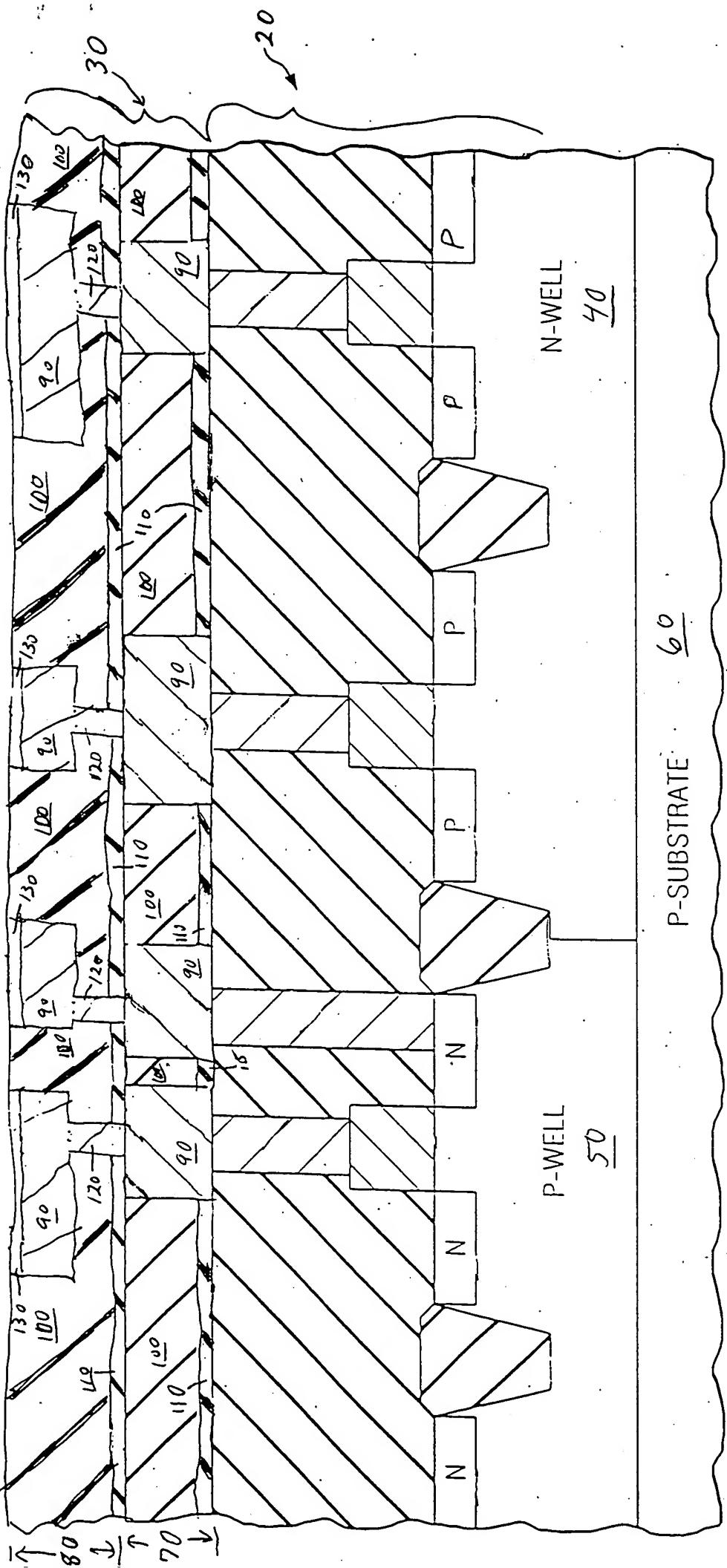


TI-35330  
RHK

10



FI 6.1

200 - Formation of barrier layer  
(optional)

210 - Formation of dielectric layer

220 - Pattern & etch of dielectric layer and ~~remove~~<sup>the</sup> the barrier layer (if used)

230 - Barrier metal and Copper deposition

240 - Copper CMP

260 - Post - CMP clean

280 - Formation of next dielectric layer

TI-35330  
RAK

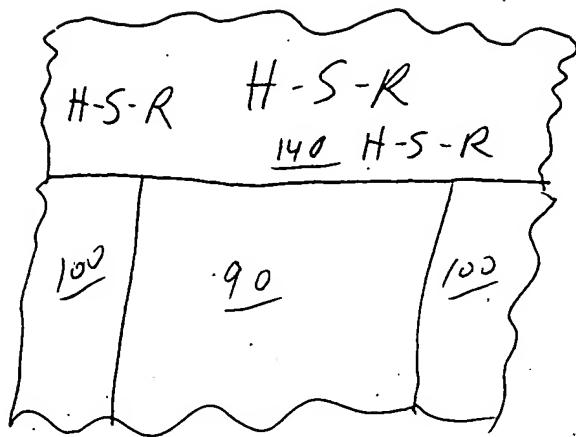


FIG. 3A

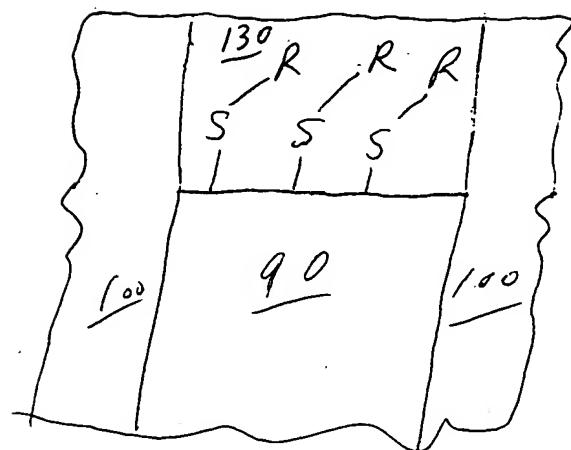
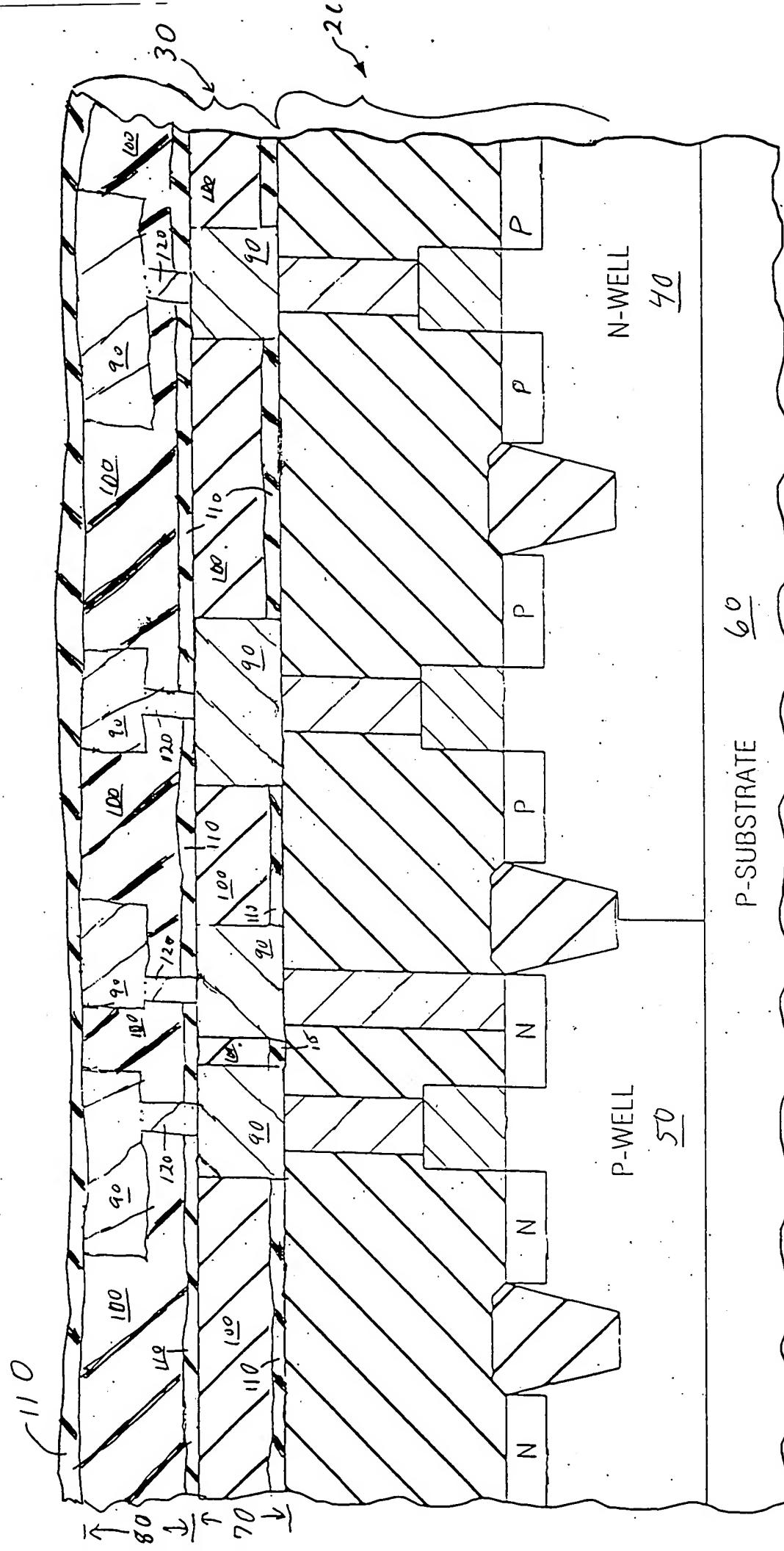


FIG. 3B

TI-355330  
RTHC

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FI 64